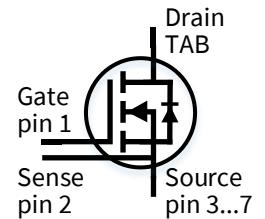


# IMBG120R030M1H

## CoolSiC™ 1200V SiC Trench MOSFET with .XT interconnection technology

### Features

- Very low switching losses
- Short circuit withstand time 3 μs
- Fully controllable dV/dt
- Benchmark gate threshold voltage,  $V_{GS(th)} = 4.5V$
- Robust against parasitic turn on, 0V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Package creepage and clearance distance > 6.1mm
- Sense pin for optimized switching performance



### Benefits

- Efficiency improvement
- Enabling higher frequency
- Increased power density
- Cooling effort reduction
- Reduction of system complexity and cost



### Potential applications

- Drives
- Infrastructure – Charger
- Energy generation - Solar string inverter and solar optimizer
- Industrial power supplies - Industrial UPS



### Product validation

Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction

**Table 1 Key Performance and Package Parameters**

Type	$V_{DS}$	$I_D$ <small><math>T_C = 25^\circ C, R_{th(j-c,max)}</math></small>	$R_{DS(on)}$ <small><math>T_{vj} = 25^\circ C, I_D = 25A, V_{GS} = 18V</math></small>	$T_{vj,max}$	Marking	Package
IMBG120R030M1H	1200V	56A	30mΩ	175°C	12M1H030	PG-TO263-7

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## Maximum ratings

## 1 Maximum ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

**Table 2 Maximum ratings**

Parameter	Symbol	Value	Unit
Drain-source voltage, $T_{vj} \geq 25^\circ\text{C}$	$V_{DSS}$	1200	V
DC drain current for $R_{th(j-c,max)}$ , limited by $T_{vj,max}$ , $V_{GS} = 18\text{V}$ , $T_C = 25^\circ\text{C}$	$I_D$	56	A
$T_C = 100^\circ\text{C}$		47	
Pulsed drain current, $t_p$ limited by $T_{vj,max}$ , $V_{GS} = 18\text{V}$	$I_{D,pulse}^1$	169	A
DC body diode forward current for $R_{th(j-c,max)}$ , limited by $T_{vj,max}$ , $V_{GS} = 0\text{V}$	$I_{SD}$	56	A
$T_C = 100^\circ\text{C}$		36	
Pulsed body diode current, $t_p$ limited by $T_{vj,max}$	$I_{SD,pulse}^1$	169	A
Gate-source voltage <sup>2</sup>			
Max transient voltage, < 1% duty cycle	$V_{GS}$	-7... 23	V
Recommended turn-on gate voltage	$V_{GS,on}$	15... 18	
Recommended turn-off gate voltage	$V_{GS,off}$	0	
Short-circuit withstand time $V_{DD} = 800\text{V}$ , $V_{DS,peak} < 1200\text{V}$ , $V_{GS,on} = 15\text{V}$ , $T_{j,start} = 25^\circ\text{C}$	$t_{SC}$	3	$\mu\text{s}$
Power dissipation, limited by $T_{vj,max}$	$P_{tot}$	300	W
$T_C = 100^\circ\text{C}$		150	
Virtual junction temperature	$T_{vj}$	-55... 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55... 150	$^\circ\text{C}$
Soldering temperature	$T_{sold}$	260	$^\circ\text{C}$
Reflow soldering (MSL1 according to JEDEC J-STD-020)			

<sup>1</sup> verified by design

<sup>2</sup> **Important note:** The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in [Application Note AN2018-09](#) must be considered to ensure sound operation of the device over the planned lifetime.

## Thermal resistances

## 2 Thermal resistances

Table 3

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
MOSFET/body diode thermal resistance, junction – case	$R_{th(j-c)}$		-	0.38	0.5	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	leaded	-	-	62	K/W

### 3 Electrical Characteristics

#### 3.1 Static characteristics

**Table 4 Static characteristics (at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified)**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 18\text{V}, I_D = 25\text{A},$ $T_{vj} = 25^\circ\text{C}$	-	30	41	mΩ
		$T_{vj} = 100^\circ\text{C}$	-	38	-	
		$T_{vj} = 175^\circ\text{C}$	-	57	-	
		$V_{GS} = 15\text{V}, I_D = 25\text{A},$ $T_{vj} = 25^\circ\text{C}$	-	39	52	
Body diode forward voltage	$V_{SD}$	$V_{GS} = 0\text{V}, I_{SD} = 25\text{A}$ $T_{vj} = 25^\circ\text{C}$	-	4.1	5.2	V
		$T_{vj} = 100^\circ\text{C}$	-	4.0	-	
		$T_{vj} = 175^\circ\text{C}$	-	3.9	-	
Gate-source threshold voltage	$V_{GS(th)}$	<i>(tested after 1 ms pulse at</i> $V_{GS} = 20\text{V})$ $I_D = 11.5\text{mA}, V_{DS} = V_{GS}$ $T_{vj} = 25^\circ\text{C}$	3.5	4.5	5.7	V
		$T_{vj} = 175^\circ\text{C}$	-	3.6	-	
Zero gate voltage drain current	$I_{DSS}$	$V_{GS} = 0\text{V}, V_{DS} = 1200\text{V}$ $T_{vj} = 25^\circ\text{C}$	-	1.1	200	μA
		$T_{vj} = 175^\circ\text{C}$	-	3.4	-	
Gate-source leakage current	$I_{GSS}$	$V_{GS} = 23\text{V}, V_{DS} = 0\text{V}$	-	-	120	nA
		$V_{GS} = -7\text{V}, V_{DS} = 0\text{V}$	-	-	-120	nA
Transconductance	$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 25\text{A}$	-	14	-	S
Internal gate resistance	$R_{G,int}$	$f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	3	-	Ω

Electrical Characteristics

3.2 Dynamic characteristics

Table 5 Dynamic characteristics (at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{DD} = 800\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	2290	-	pF
Output capacitance	$C_{oss}$		-	105	-	
Reverse capacitance	$C_{rss}$		-	11	-	
$C_{oss}$ stored energy	$E_{oss}$		-	44	-	$\mu\text{J}$
Total gate charge	$Q_G$	$V_{DD} = 800\text{V}, I_D = 25\text{A},$ $V_{GS} = 0/18\text{V}, \text{turn-on pulse}$	-	63	-	nC
Gate to source charge	$Q_{GS,pl}$		-	18	-	
Gate to drain charge	$Q_{GD}$		-	15	-	

Electrical Characteristics

3.3 Switching characteristics

Table 6 Switching characteristics, Inductive load <sup>3</sup>

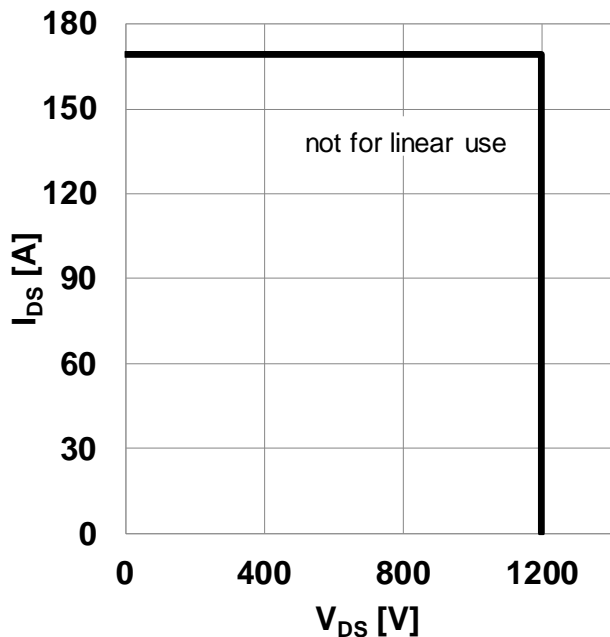
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>MOSFET Characteristics, <math>T_{vj} = 25^{\circ}\text{C}</math></b>						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{V}, I_D = 25\text{A},$ $V_{GS} = 0/18\text{V}, R_{G,ext} = 2\Omega,$ $L_{\sigma} = 40\text{nH},$ diode: body diode at $V_{GS} = 0\text{V}$ see Fig. E	-	11	-	ns
Rise time	$t_r$		-	14	-	
Turn-off delay time	$t_{d(off)}$		-	25	-	
Fall time	$t_f$		-	11	-	
Turn-on energy	$E_{on}$		-	268	-	$\mu\text{J}$
Turn-off energy	$E_{off}$		-	69	-	
Total switching energy	$E_{tot}$	-	337	-		
<b>Body Diode Characteristics, <math>T_{vj} = 25^{\circ}\text{C}</math></b>						
Diode reverse recovery charge	$Q_{rr}$	$V_{DD} = 800\text{V}, I_{SD} = 25\text{A},$ $V_{GS}$ at diode = $0\text{V},$ $di_f/dt = 1000\text{A}/\mu\text{s},$ $Q_{rr}$ includes also $Q_C,$ see Fig. C	-	300	-	nC
Diode peak reverse recovery current	$I_{rrm}$		-	5.8	-	A

**MOSFET Characteristics,  $T_{vj} = 175^{\circ}\text{C}$**

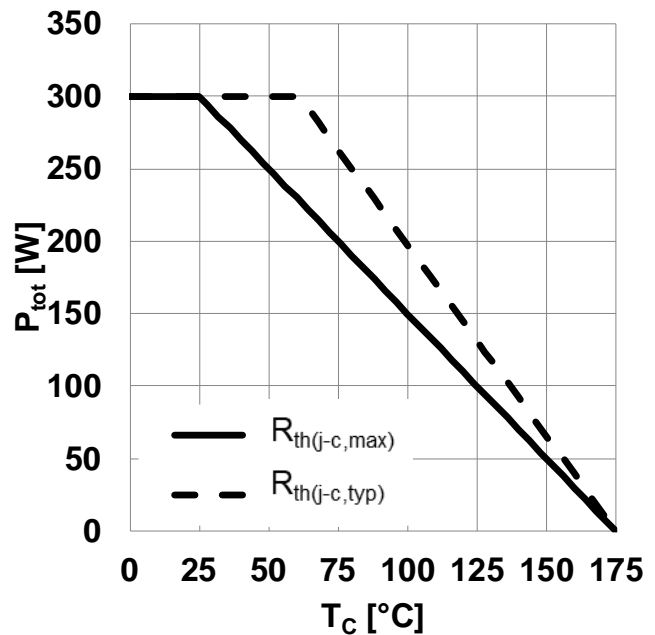
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{V}, I_D = 25\text{A},$ $V_{GS} = 0/18\text{V}, R_{G,ext} = 2\Omega,$ $L_{\sigma} = 40\text{nH},$ diode: body diode at $V_{GS} = 0\text{V}$ see Fig. E	-	11	-	ns
Rise time	$t_r$		-	33	-	
Turn-off delay time	$t_{d(off)}$		-	25	-	
Fall time	$t_f$		-	11	-	
Turn-on energy	$E_{on}$		-	411	-	$\mu\text{J}$
Turn-off energy	$E_{off}$		-	80	-	
Total switching energy	$E_{tot}$	-	491	-		
<b>Body Diode Characteristics, <math>T_{vj} = 175^{\circ}\text{C}</math></b>						
Diode reverse recovery charge	$Q_{rr}$	$V_{DD} = 800\text{V}, I_{SD} = 25\text{A},$ $V_{GS}$ at diode = $0\text{V},$ $di_f/dt = 1000\text{A}/\mu\text{s},$ $Q_{rr}$ includes also $Q_C,$ see Fig. C	-	375	-	nC
Diode peak reverse recovery current	$I_{rrm}$		-	8	-	A

<sup>3</sup> The chip technology was characterized up to 200 kV/ $\mu\text{s}$ . The measured dV/dt was limited by measurement test setup and package.

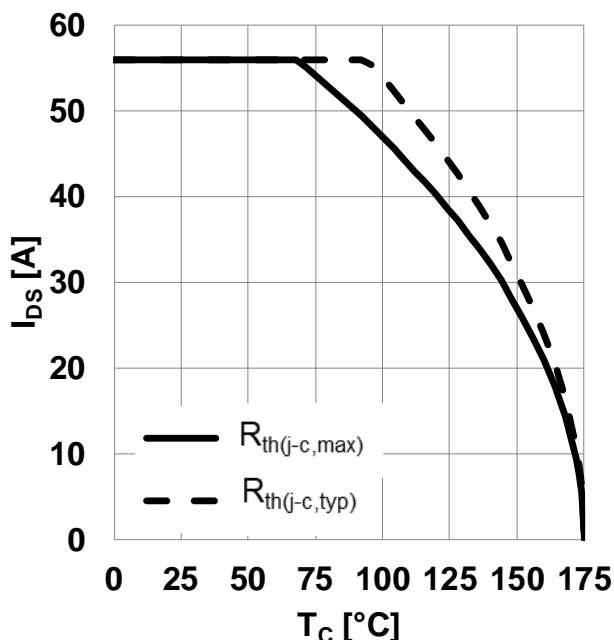
## 4 Electrical characteristic diagrams



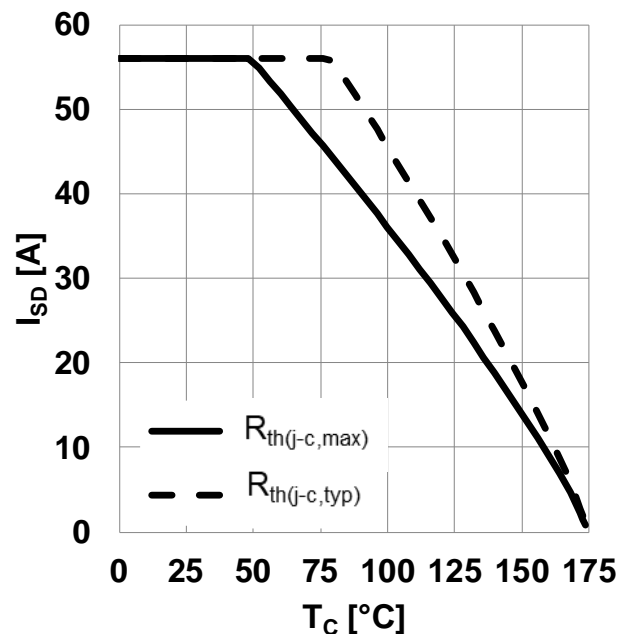
**Figure 1** Safe operating area (SOA)  
( $V_{GS} = 0/18V$ ,  $T_c = 25^\circ C$ ,  $T_j \leq 175^\circ C$ )



**Figure 2** Power dissipation as a function of case temperature limited by bond wire  
( $P_{tot} = f(T_C)$ )



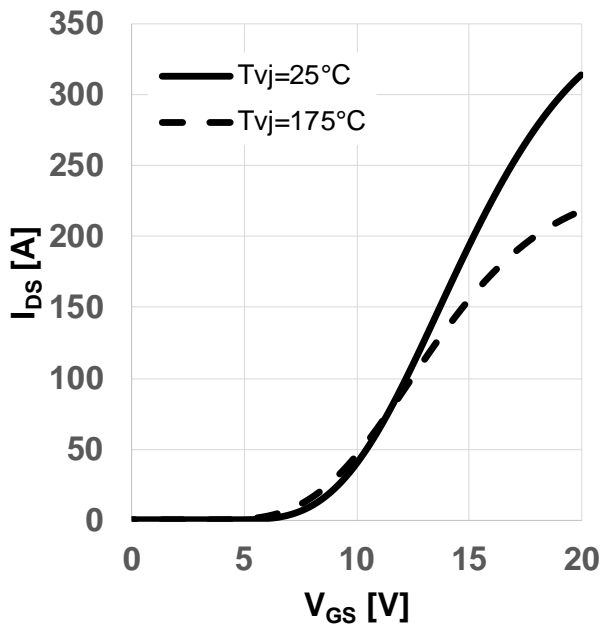
**Figure 3** Maximum DC drain to source current as a function of case temperature limited by bond wire ( $I_{DS} = f(T_C)$ )



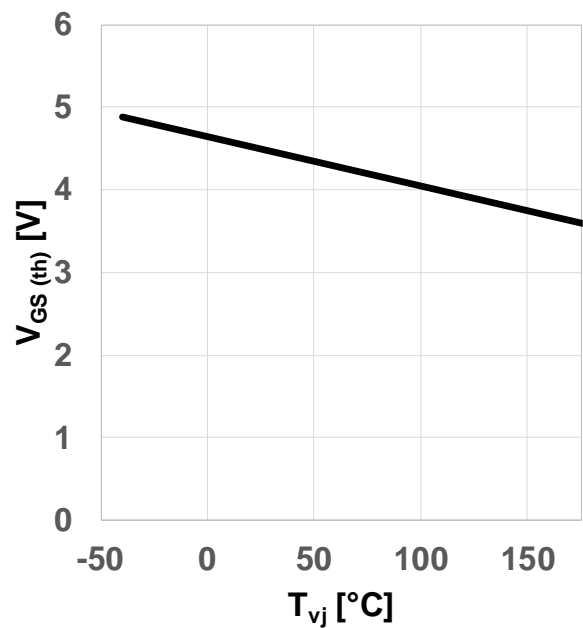
**Figure 4** Maximum source to drain current as a function of case temperature limited by bond wire ( $I_{SD} = f(T_C)$ ,  $V_{GS} = 0V$ )



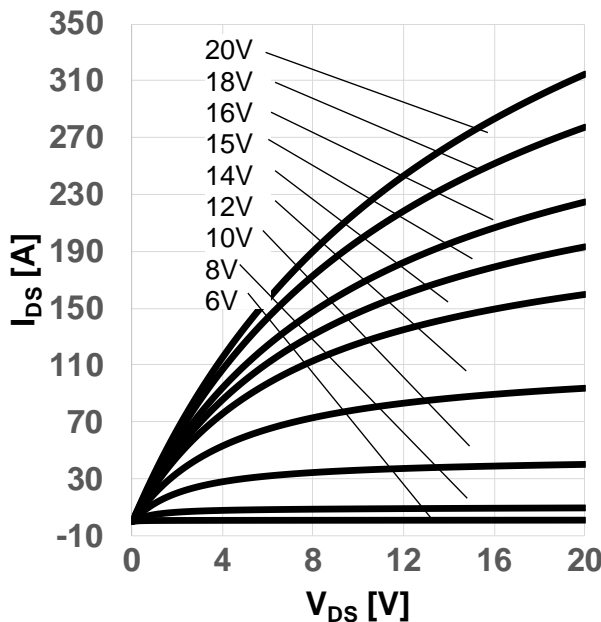
**Electrical characteristic diagrams**



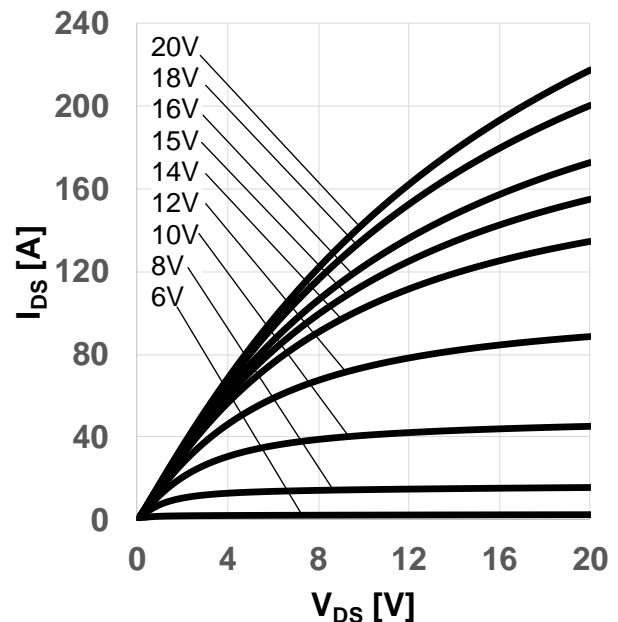
**Figure 5** Typical transfer characteristic  
 ( $I_{DS} = f(V_{GS}), V_{DS} = 20V, t_P = 20\mu s$ )



**Figure 6** Typical gate-source threshold voltage as a function of junction temperature  
 ( $V_{GS(th)} = f(T_{vj}), I_{DS} = 11.5mA, V_{GS} = V_{DS}$ )

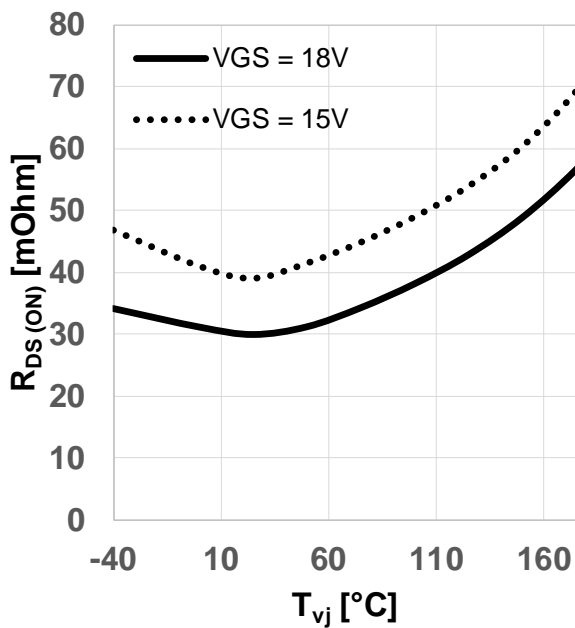


**Figure 7** Typical output characteristic,  $V_{GS}$  as parameter  
 ( $I_{DS} = f(V_{DS}), T_{vj}=25°C, t_P = 20\mu s$ )

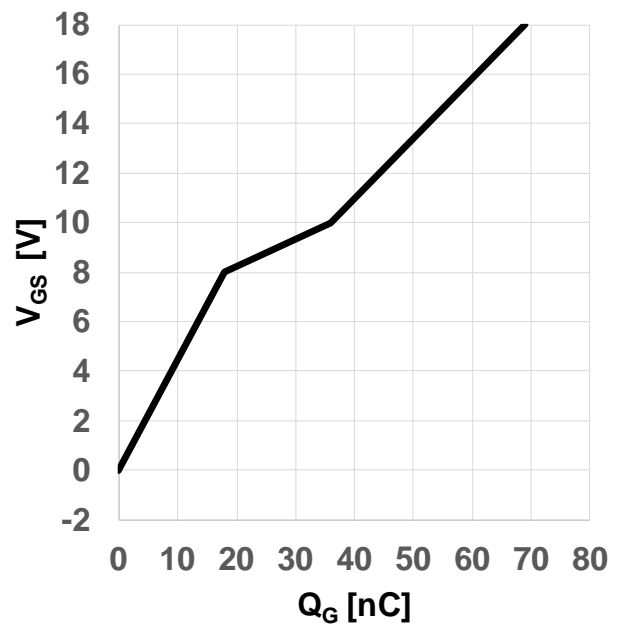


**Figure 8** Typical output characteristic,  $V_{GS}$  as parameter  
 ( $I_{DS} = f(V_{DS}), T_{vj}=175°C, t_P = 20\mu s$ )

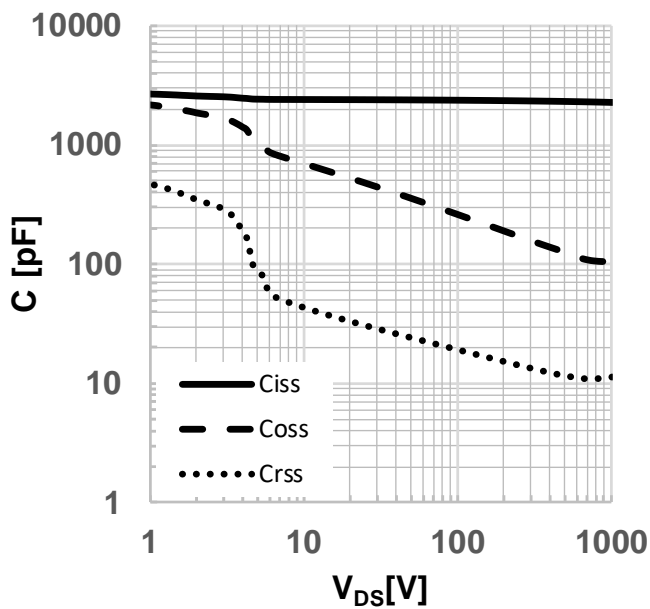
Electrical characteristic diagrams



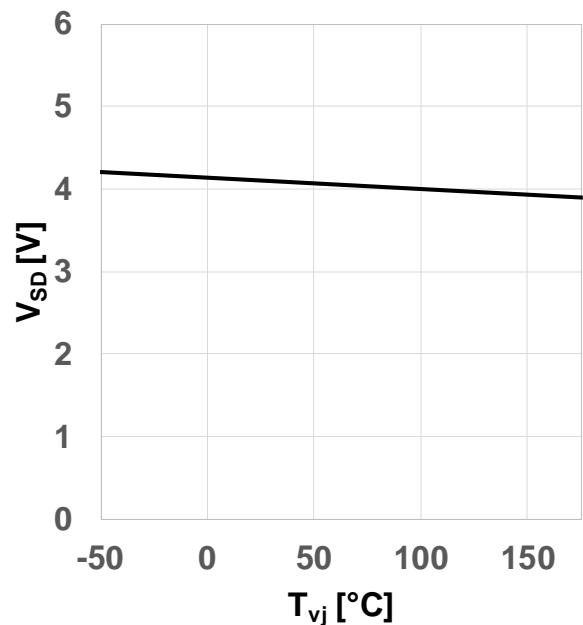
**Figure 9** Typical on-resistance as a function of junction temperature  
 $(R_{DS(on)} = f(T_{vj}), I_{DS} = 25A)$



**Figure 10** Typical gate charge  
 $(V_{GS} = f(Q_G), I_{DS} = 25A, V_{DS} = 800V, \text{turn-on pulse})$

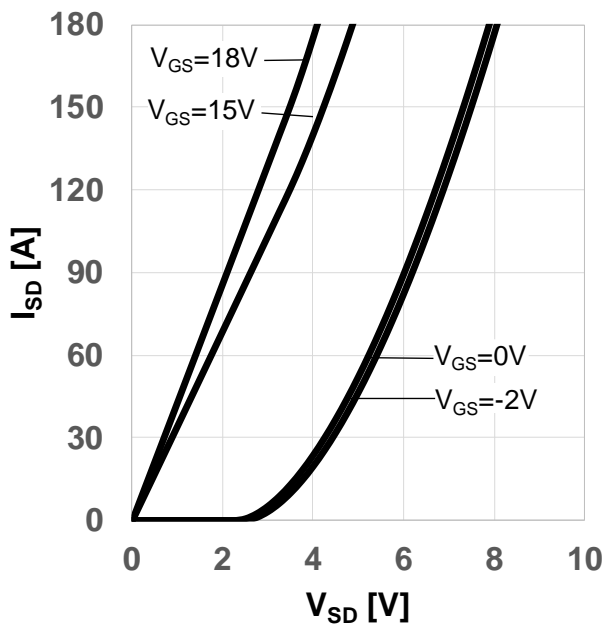


**Figure 11** Typical capacitance as a function of drain-source voltage  
 $(C = f(V_{DS}), V_{GS} = 0V, f = 1MHz)$

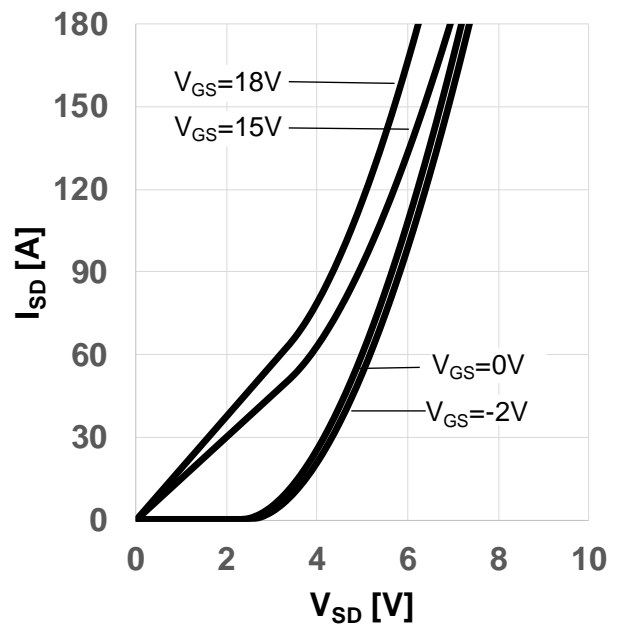


**Figure 12** Typical body diode forward voltage as function of junction temperature  
 $(V_{SD} = f(T_{vj}), V_{GS} = 0V, I_{SD} = 25A)$

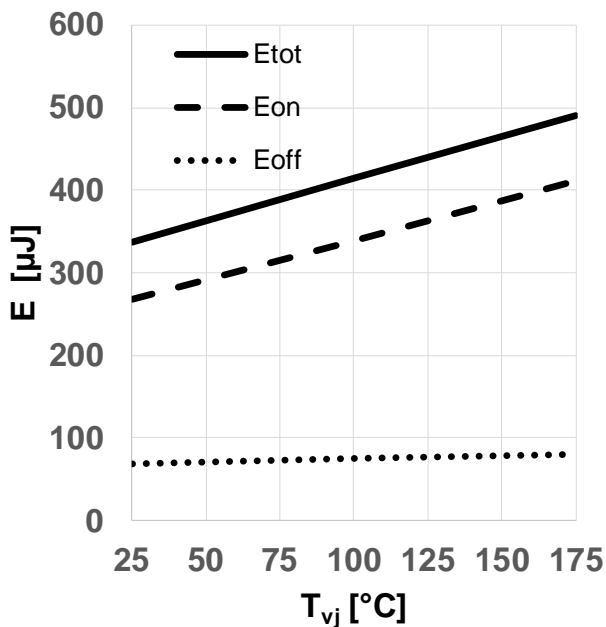
Electrical characteristic diagrams



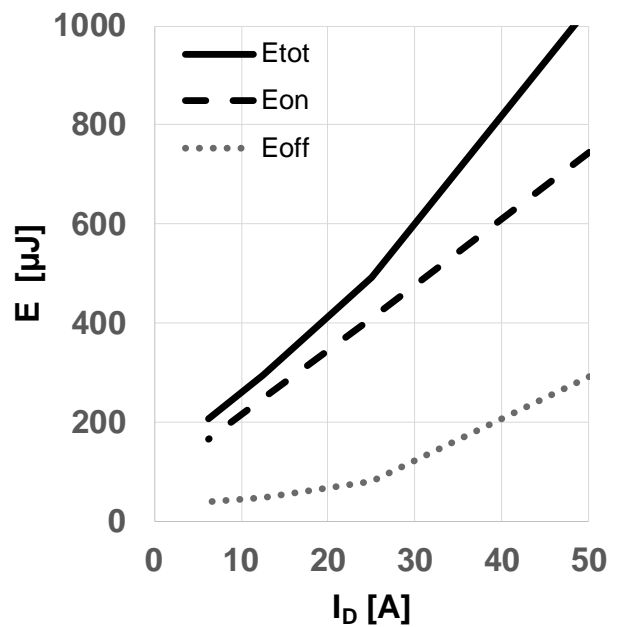
**Figure 13** Typical body diode forward current as function of forward voltage,  $V_{GS}$  as parameter  
( $I_{SD} = f(V_{SD})$ ,  $T_{vj} = 25^{\circ}\text{C}$ ,  $t_P = 20\mu\text{s}$ )



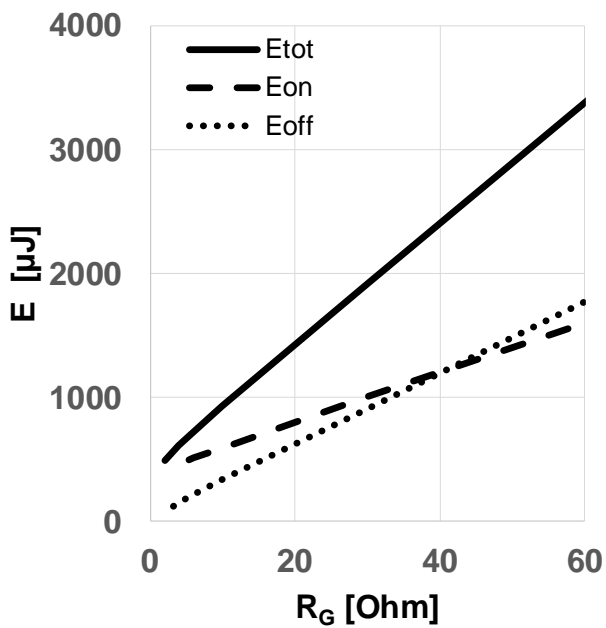
**Figure 14** Typical body diode forward current as function of forward voltage,  $V_{GS}$  as parameter  
( $I_{SD} = f(V_{SD})$ ,  $T_{vj} = 175^{\circ}\text{C}$ ,  $t_P = 20\mu\text{s}$ )



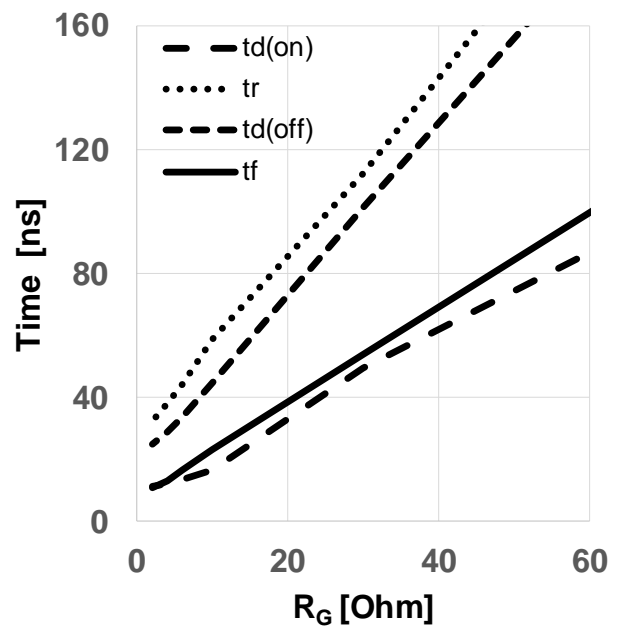
**Figure 15** Typical switching energy losses as a function of junction temperature  
( $E = f(T_{vj})$ ,  $V_{DD} = 800\text{V}$ ,  $V_{GS} = 0\text{V}/18\text{V}$ ,  $R_{G,ext} = 2\Omega$ ,  $I_D = 25\text{A}$ , ind. load, test circuit in Fig. E, diode: body diode at  $V_{GS} = 0\text{V}$ )



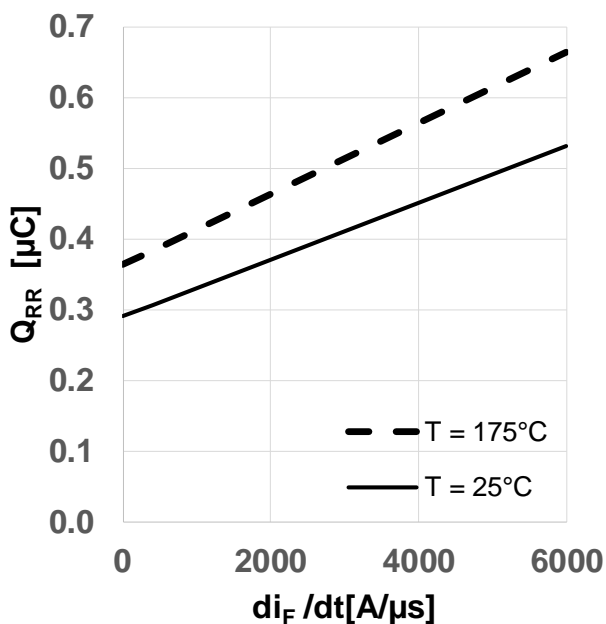
**Figure 16** Typical switching energy losses as a function of drain-source current  
( $E = f(I_{DS})$ ,  $V_{DD} = 800\text{V}$ ,  $V_{GS} = 0\text{V}/18\text{V}$ ,  $R_{G,ext} = 2\Omega$ ,  $T_{vj} = 175^{\circ}\text{C}$ , ind. load, test circuit in Fig. E, diode: body diode at  $V_{GS} = 0\text{V}$ )



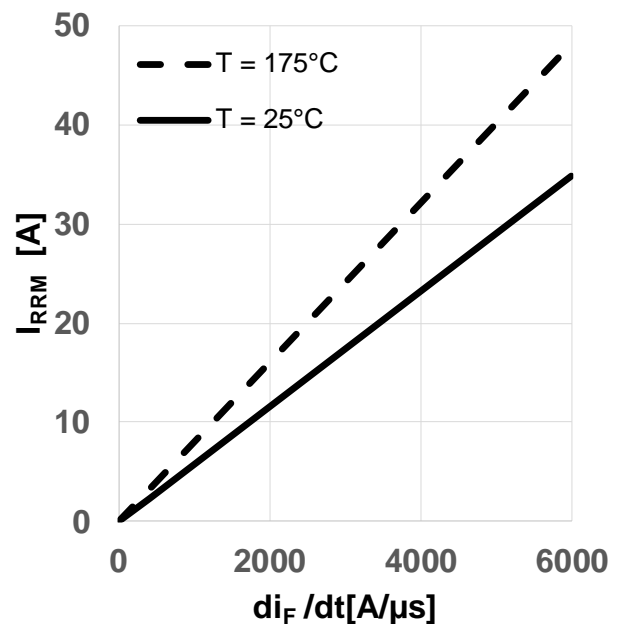
**Figure 17 Typical switching energy losses as a function of gate resistance**  
 $(E = f(R_{G,ext}), V_{DD} = 800V, V_{GS} = 0V/18V,$   
 $I_D = 25A, T_{vj} = 175^\circ C, \text{ind. load, test circuit}$   
in Fig. E, diode: body diode at  $V_{GS} = 0V)$



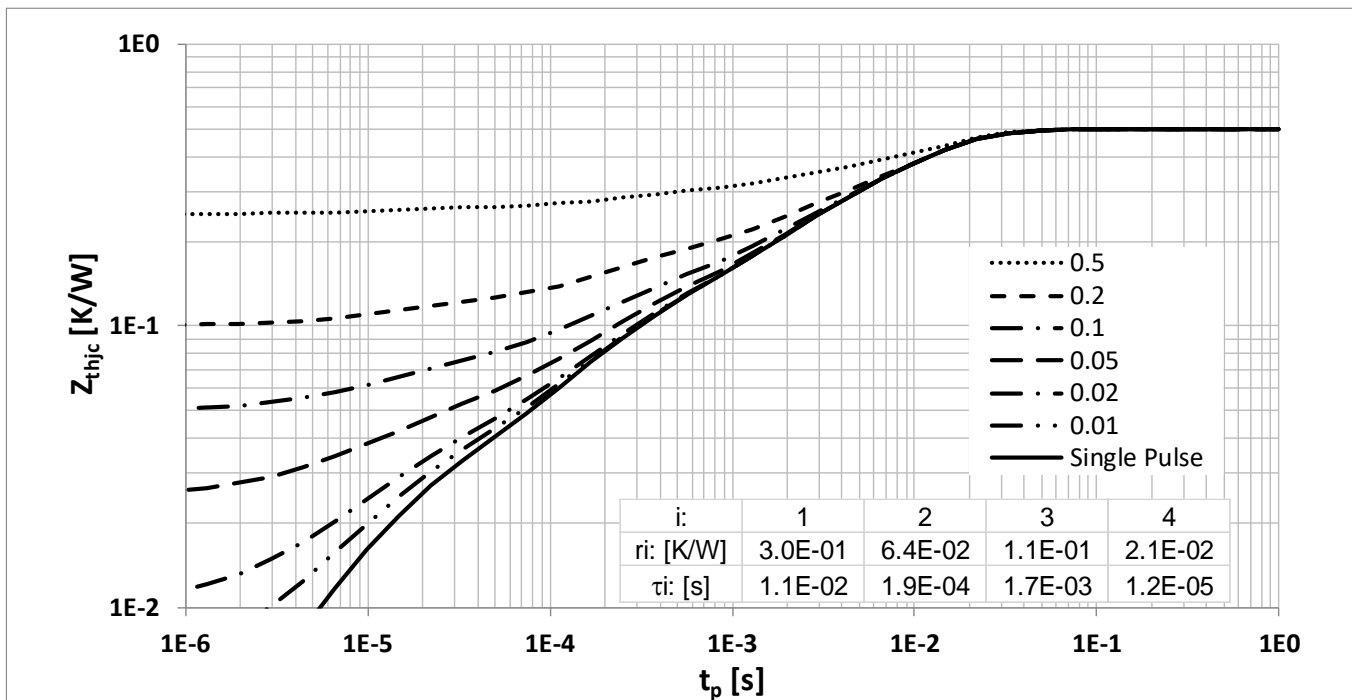
**Figure 18 Typical switching times as a function of gate resistor**  
 $(t = f(R_{G,ext}), V_{DD} = 800V, V_{GS} = 0V/18V,$   
 $I_D = 25A, T_{vj} = 175^\circ C, \text{ind. load, test circuit}$   
in Fig. E, diode: body diode at  $V_{GS} = 0V)$



**Figure 19 Typical reverse recovery charge as a function of diode current slope**  
 $(Q_{rr} = f(di_i/dt), V_{DD} = 800V, V_{GS} = 0V/18V,$   
 $I_D = 25A, \text{ind. load, test circuit in Fig.E,}$   
body diode at  $V_{GS} = 0V)$



**Figure 20 Typical reverse recovery current as a function of diode current slope**  
 $(I_{rrm} = f(di_i/dt), V_{DD} = 800V, V_{GS} = 0V/18V,$   
 $I_D = 25A, \text{ind. load, test circuit in Fig.E,}$   
body diode at  $V_{GS} = 0V)$



**Figure 21 Max. transient thermal resistance (MOSFET/diode)**  
 $(Z_{th(j-c,max)} = f(t_p), \text{ parameter } D = t_p/T, \text{ thermal equivalent circuit in Fig. D})$

5 Package drawing

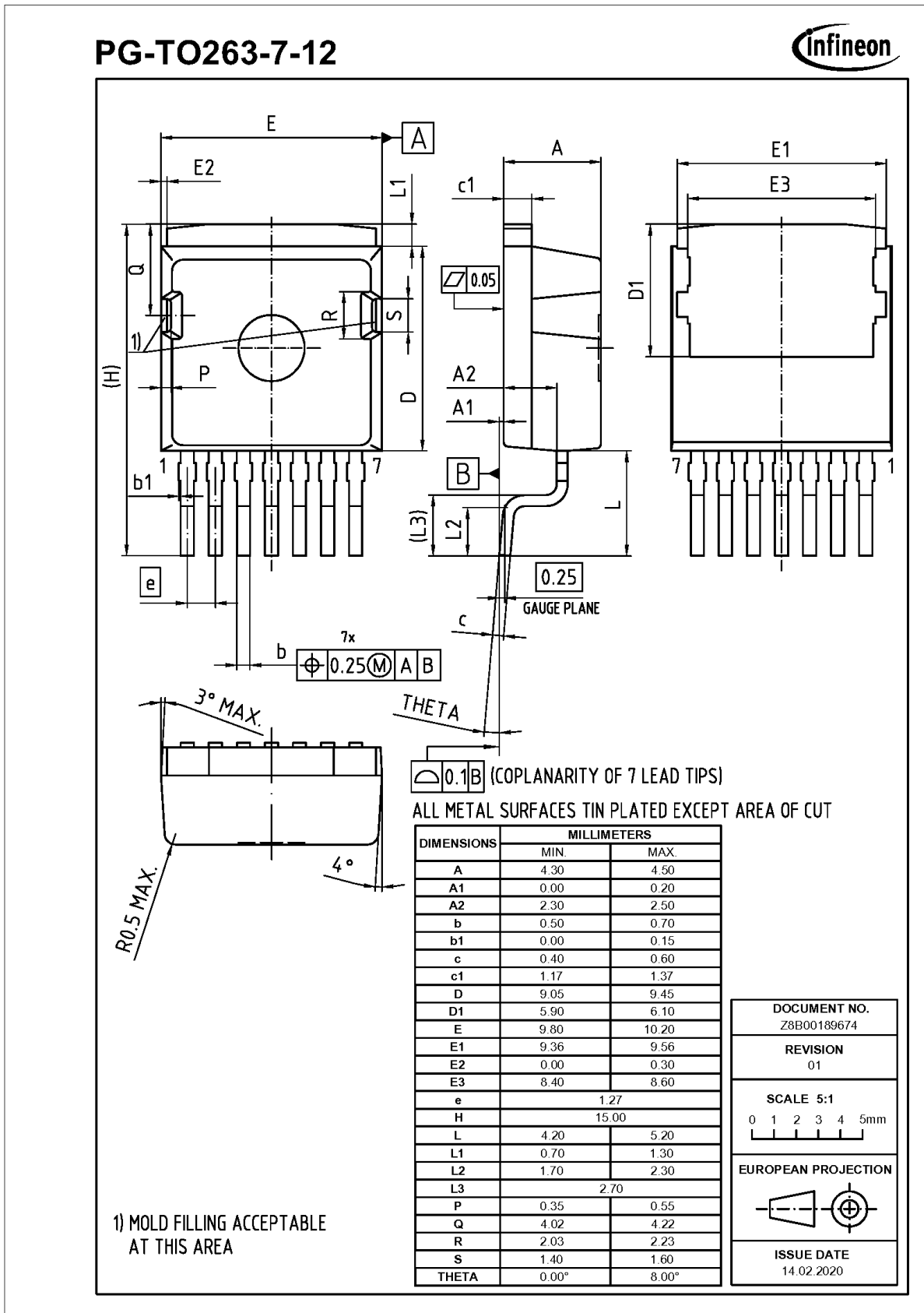


Figure 22 Package drawing

Test conditions

6 Test conditions



Figure 23 Test conditions

**Revision history**

**Revision history**

<b>Document version</b>	<b>Date of release</b>	<b>Description of changes</b>
2.1	2020-09-01	Final Datasheet
2.2	2020-12-11	Correction of circuit symbol on page 1



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## Published by

**Infineon Technologies AG**

**81726 München, Germany**

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